# N-Channel 150-V (D-S) MOSFET

### **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

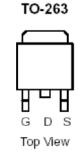
## **Typical Applications:**

- · LED Inverter Circuits
- Inrush Limiter and Hot Swap Circuits
- 48V-Input DC/DC Conversion Circuits

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)	
150	19 @ V <sub>GS</sub> = 10V	100 <sup>a</sup>	
130	$24 @ V_{GS} = 6.5V$	100	







ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)							
Parameter			Limit	Units			
Drain-Source Voltage			150	\/			
Gate-Source Voltage			±20	ľ			
Continuous Drain Current a	T <sub>C</sub> =25°C	I <sub>D</sub>	100				
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	400	Α			
Continuous Source Current (Diode Conduction) a	T <sub>C</sub> =25°C	I <sub>S</sub>	100	Α			
Power Dissipation <sup>a</sup>	T <sub>C</sub> =25°C	$P_D$	300	W			
Operating Junction and Storage Temperature Range		$T_J$ , $T_{stg}$	-55 to 175	°C			

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient °	$R_{\theta JA}$	62.5	°C/W		
Maximum Junction-to-Case	$R_{ heta JC}$	0.5	C/VV		

#### Notes

- a. Package Limited
- b. Pulse width limited by maximum junction temperature
- c. Surface Mounted on 1" x 1" FR4 Board.

#### **Electrical Characteristics**

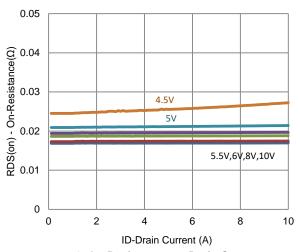
Parameter	Symbol	Symbol Test Conditions		Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	1			V	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	lana	$V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zelo Gate Voltage Dialii Current	I <sub>DSS</sub>	$V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	uA	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	20			Α	
Drain Course On Besistance a	r	$V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$			19	mΩ	
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = 6 \text{ V}, I_{D} = 16 \text{ A}$			24	11177	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		38		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = 50 \text{ A}, V_{GS} = 0 \text{ V}$		1.1		V	
		Dynamic <sup>b</sup>					
Total Gate Charge	$Q_g$	$V_{DS} = 50 \text{ V}, V_{GS} = 6.5 \text{ V},$		30		nC	
Gate-Source Charge	$Q_gs$	$V_{DS} = 30 \text{ V}, V_{GS} = 6.3 \text{ V},$ $I_{D} = 20 \text{ A}$		9.1			
Gate-Drain Charge	$Q_gd$	10 = 20 / (		12			
Turn-On Delay Time	$t_{d(on)}$	V 50 V B = 25 O		17			
Rise Time	t <sub>r</sub>	$V_{DS} = 50 \text{ V}, R_{L} = 2.5 \Omega,$ $I_{D} = 20 \text{ A},$		15		no	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		48		ns	
Fall Time	t <sub>f</sub>	V GEN = 10 V, T GEN 0 12		32			
Input Capacitance	C <sub>iss</sub>			2236			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$	_	228		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			46			

#### Notes

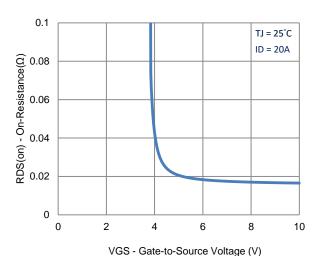
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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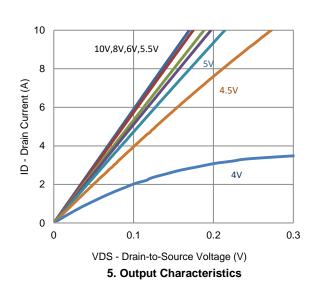
# **Typical Electrical Characteristics**

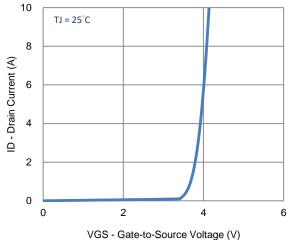


#### 1. On-Resistance vs. Drain Current

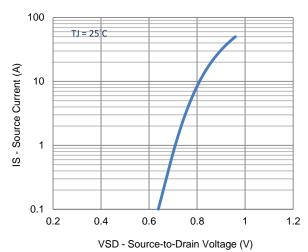


3. On-Resistance vs. Gate-to-Source Voltage

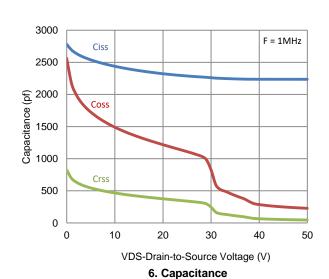




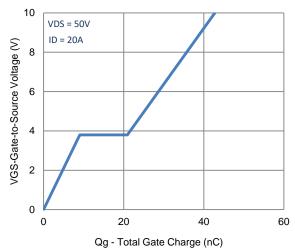
2. Transfer Characteristics



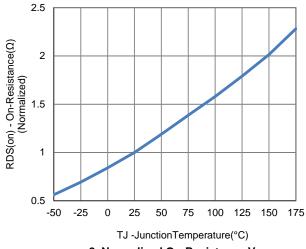
4. Drain-to-Source Forward Voltage



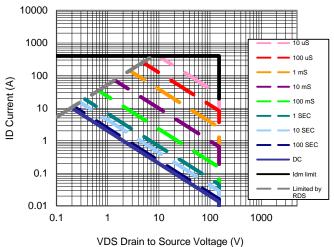
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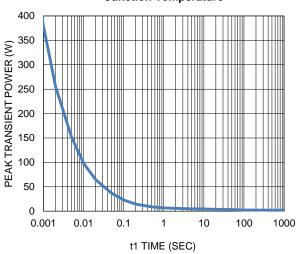
7. Gate Charge



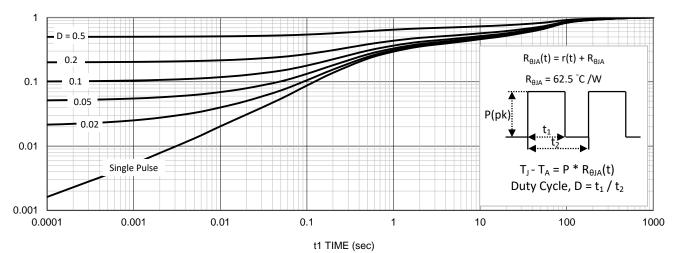
8. Normalized On-Resistance Vs Junction Temperature



9. Safe Operating Area

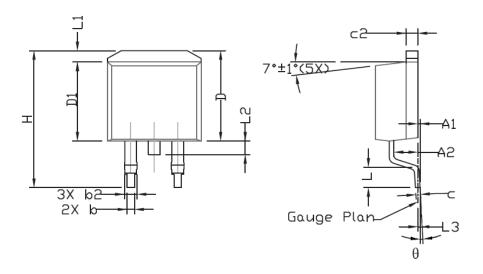


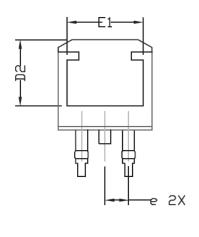
10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

# **Package Information**





CVAAREI	DIMENS:	IONAL F	REQMTS	INCHES REQMTS		
SYMBOL	MIN	NDM	MAX	MIN	NDM	MAX
Α	4,30	4.57	4,72	0.169	0.180	0.186
A1	0		0,25	0		0.010
A2	2,47	2,57	2,67	0.097	0.101	0.105
b	0.69	0,813	0.94	0.027	0.032	0.037
b2	1,17	1.27	1,45	0.046	0.050	0.057
C	0.48	0,50	0.60	0.019	0.020	0.024
c2	1,17	1.27	1.37	0.046	0.050	0,054
D	9,80	10.05	10.30	0.386	0,396	0.406
D1	8,64	8,78	9,65	0,340	0,346	0,380
D2	7.12	7,37	7,62	0.280	0,290	0,300
E	9,70	10.15	10.54	0.382	0,400	0.415
E1	8,00	8.20	8,40	0.315	0,323	0,331
е	2.54 BSC			0.	100 BSC	,
H	14,99	15,24	15.49	0.590	0.600	0.610
L	1,78	2,29	2.79	0.070	0.090	0.110
L1	1.02	1.27	1.52	0.040	0.050	0,060
L2			1.75			0.069
L3		0,254			0.010	
θ	0°		8.	0°		8.